# 64K x 18 Bit Synchronous Pipelined Cache Tag RAM

The MCM69T618 is a 1M-bit synchronous fast static RAM with integrated tag compare function. It is designed to address tag RAM for 512KB, 1MB, or 2MB secondary cache as well as to be used as a data RAM for 512KB caches. This device is organized as 64K words of 18 bits each. It integrates input registers, output registers, tag comparators, and high speed SRAM onto a single monolithic circuit for reduced parts count in cache tag RAM applications. Synchronous design allows precise cycle control with the use of an external clock (K). BiCMOS circuitry reduces the overall power consumption of the integrated functions for greater reliability.

Addresses (SA), data inputs (DQ), write enable (SW), and chip enable (SE0 and SE1) are all controlled through positive—edge—triggered noninverting registers. Data enable (DE) is sampled on the rising clock edge while output enable (G) and match output enable (MG) are asynchronous.

Write cycles are internally self–timed and initiated by the rising edge of the clock (K) input. This feature eliminates complex off–chip write pulse generation and provides increased timing flexibility for incoming signals.

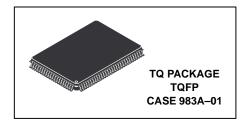
For read cycles, pipelined SRAM output data is temporarily stored by an edge—triggered output register and then released to the output buffers at the next rising edge of clock (K).

Compare cycles begin as read cycles with output disabled, so compare data can be loaded into the input register. The comparator compares the read data with the registered input data, and a match signal is generated. The match output is also stored by an output register and released to the match output buffer at the next rising edge of clock (K).

The MCM69T618 operates from a single 3.3 V power supply and all inputs and outputs are LVTTL compatible.

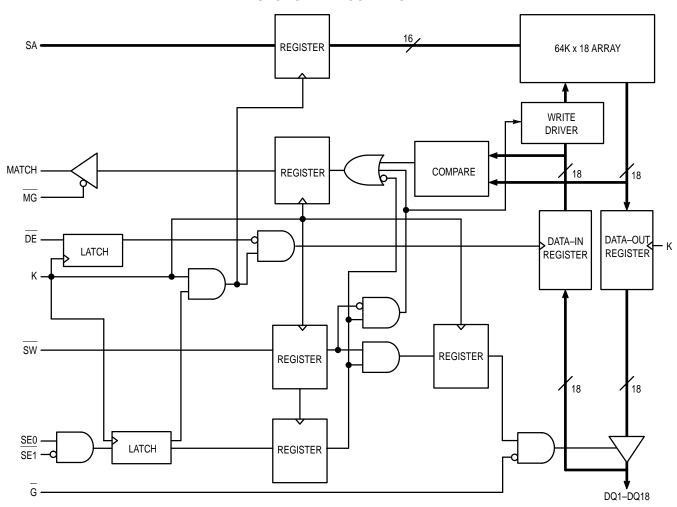
- MCM69T618–5 = 5 ns Clock–to–Match / 10 ns cycle
- Single 3.3 V + 10%, 5% Power Supply
- Pipelined Data Comparator
- Pipelined Chip Enable and Write Enable for Data (DQ) Output Enable Path
- 64K x 18 Organization Supports Up to 2MB Cache
- Synchronous Data Input Register Load Enable (DE)
- Internally Self-Timed Write Cycle
- Asynchronous Data I/O Output Enable (G)
- Asynchronous Match Output Enable (MG)
- 100-Pin TQFP Package

### MCM69T618



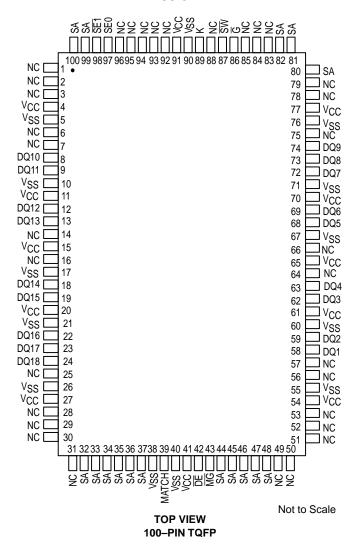
REV 5 12/23/97

#### **FUNCTIONAL BLOCK DIAGRAM**



MCM69T618 MOTOROLA FAST SRAM

#### **PIN ASSIGNMENT**



MOTOROLA FAST SRAM

MCM69T618

#### PIN DESCRIPTIONS

Pin Locations	Symbol	Type	Description			
42	DE	Input	Data Enable Input: Latched on the rising clock edge, active low. The data input register is only updated when DE is low.			
8, 9, 12, 13, 18, 19, 22, 23, 24, 58, 59, 62, 63, 68, 69, 72, 73, 74	DQ1 – DQ18	I/O	Synchronous Data I/O: For write cycles, registered on the rising clock edge. Two cycles after a read command, the read data is output on the DQ pins provided that G is low. On the same cycle of a write command, the write d is input on the DQ signals.			
86	G	Input	Output Enable: Asynchronous pin, active low. <u>G</u> must be low for read data to be output two cycles after a read command. If G is high, the data output DQ will remain in high impedance even if a read command occurs internally.			
89	К	Input	Clock: All the signals except G and MG are controlled by the clock.			
39	MATCH	Output	Two cycles after a compare cycle and if MG is low, MATCH will be high if the data presented to the DQ inputs matches the data stored in the RAM. MATCH will be low if the data does not match.			
43	MG	Input	Match Output Enable: Asynchronous pin, active low. When MG is low, the MATCH output driver is on, otherwise the MATCH output driver is in high impedance.			
32, 33, 34, 35, 36, 37, 44, 45, 46, 47, 48, 80, 81, 82, 99, 100	SA	Input	Synchronous Address Inputs: Registered on the rising clock edge. The address pins select one of the 64K tag entries.			
97	SE0	Input	Synchronous Chip Enable: Registered on the rising clock edge, active high.			
98	SE1	Input	Synchronous Chip Enable: Registered on the rising clock edge, active low.			
87	SW	Input	Synchronous Write: Registered on the rising clock edge, active low. The SW input specifies whether a read or write cycle is to occur when the chip is enabled. A write command should not be issued within three cycles of a read command unless G is high or output drive contention may occur.			
4, 11, 15, 20, 27, 41, 54, 61, 65, 70, 77, 91	Vcc	Supply	Power Supply: 3.3 V + 10%, – 5%.			
5, 10, 17, 21, 26, 38, 40, 55, 60, 67, 71, 76, 90	V <sub>SS</sub>	Supply	Ground.			
1, 2, 3, 6, 7, 14, 16, 25, 28, 29, 30, 31, 49, 50, 51, 52, 53, 56, 57, 64, 66, 75, 78, 79, 83, 84, 85, 88, 92, 93, 94, 95, 96	NC	_	No Connection: There is no connection to the chip.			

MCM69T618 MOTOROLA FAST SRAM

#### TRUTH TABLE (See Notes 1 through 4)

Next Cycle	SE	sw	DE	MG	G	Match	DQ
Read	0	1	Х	Х	0	_	Data Out
Write	0	0	0	Х	1	_	Data In
Compare	0	1	0	0	1	Data Out	Data In
Fill Write	0	0	1	Х	1	_	High-Z
Deselected (Match Out)	1	Х	Х	0	Х	Data High	High-Z
Deselected	1	Х	Х	1	Х	High–Z	High-Z

#### NOTES:

- 1. X = Don't Care. 1 = logic high. 0 = logic low.
- 2. SE low is defined as SE1 = 0 and SE0 = 1. SE high is defined as SE1 =  $\frac{1}{2}$  or SE0 = 0.
- 3. G and MG are asynchronous signals and are not sampled by the clock K. G drives the bus immediately (tGLQX) when G goes low.
- 4. On write cycles that follow read cycles, G must be negated prior to the start of the write cycle to ensure proper write data setup times. G must also remain negated at the completion of the write cycle to ensure proper write data hold times.

#### **ABSOLUTE MAXIMUM RATINGS (See Note)**

Rating	Symbol	Value	Unit
Power Supply Voltage	VCC	- 0.5 to + 4.6	V
Voltage Relative to VSS for Any Pin Except VCC	V <sub>in</sub> , V <sub>out</sub>	V <sub>CC</sub> + 0.5	V
Output Current (per I/O)	l <sub>out</sub>	± 20	mA
Package Power Dissipation	PD	1.6	W
Temperature Under Bias	T <sub>bias</sub>	- 10 to + 85	°C
Storage Temperature	T <sub>stg</sub>	- 55 to + 125	°C

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high-impedance circuit.

NOTE: Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to RECOMMENDED OPER-ATING CONDITIONS. Exposure to higher than recommended voltages for extended periods of time could affect device reliability.

#### PACKAGE THERMAL CHARACTERISTICS (See Note 1)

Rating		Symbol	Max	Unit	Notes
Junction to Ambient (@ 200 lfm)	Single–Layer Board Four–Layer Board	$R_{ heta JA}$	40 25	°C/W	2
Junction to Board (Bottom)		$R_{\theta JB}$	17	°C/W	3
Junction to Case (Top)		$R_{ heta JC}$	9	°C/W	4

#### NOTES:

- 1. Junction temperature is a function of on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, board population, and board thermal resistance.
- 2. Per SEMI G38-87.
- 3. Indicates the average thermal resistance between the die and the printed circuit board.
- 4. Indicates the average thermal resistance between the die and the case top surface via the cold plate method (MIL SPEC-883 Method 1012.1).

MOTOROLA FAST SRAM MCM69T618

#### DC OPERATING CONDITIONS AND CHARACTERISTICS

 $(V_{CC} = 3.3 \text{ V} + 10\%, -5\%, T_{J} = 20 \text{ to } 110^{\circ}\text{C}, \text{Unless Otherwise Noted})$ 

#### **RECOMMENDED OPERATING CONDITIONS** (Voltages Referenced to $V_{SS} = 0 V$ )

Parameter	Symbol	Min	Тур	Max	Unit
Supply Voltage	Vcc	3.135	3.3	3.6	V
Operating Temperature	TJ	20	_	110	°C
Input Low Voltage	V <sub>IL</sub>	- 0.5*	_	0.8	V
Input High Voltage	VIH	2.0	_	V <sub>CC</sub> + 0.5**	V

#### DC CHARACTERISTICS AND SUPPLY CURRENTS

Parameter	Symbol	Min	Тур	Max	Unit	Notes
Input Leakage Current (0 V ≤ V <sub>in</sub> ≤ V <sub>CC</sub> )	l <sub>lkg(l)</sub>	_	_	± 1	μΑ	
Output Leakage Current (0 V ≤ V <sub>in</sub> ≤ V <sub>CC</sub> )	llkg(O)	_	_	± 1	μΑ	
AC Supply Current (Device Selected, All Outputs Open, All Inputs Toggling at $V_{in} \leq V_{IL}$ or $\geq V_{IH}$ Cycle Time $\geq t_{KHKH}$ min)	ICCA	_	_	240	mA	
CMOS Standby Supply Current (Deselected, Clock (K) Cycle Time $\geq$ t <sub>KHKH</sub> , All Inputs Toggling at CMOS Levels V <sub>in</sub> $\leq$ V <sub>SS</sub> + 0.2 V or $\geq$ V <sub>CC</sub> $-$ 0.2 V)	I <sub>SB1</sub>	_	_	130	mA	1
Clock Running Supply Current (Deselected, Clock (K) Cycle Time $\geq$ t <sub>KHKH</sub> , All Other Inputs Held to Static CMOS Levels $V_{in} \leq V_{SS} + 0.2 \text{ V or } \geq V_{CC} - 0.2 \text{ V})$	I <sub>SB2</sub>	_	_	45	mA	1
Output Low Voltage (I <sub>OL</sub> = 8 mA)	VOL	_	_	0.4	V	
Output High Voltage (I <sub>OH</sub> = -4 mA)	Voн	2.4	_	_	V	

#### NOTE:

#### $\textbf{CAPACITANCE} \; (\text{f} = 1.0 \; \text{MHz}, \; \text{dV} = 3.0 \; \text{V}, \; \text{T}_{\mbox{A}} = 25 ^{\circ} \mbox{C}, \; \text{Periodically Sampled Rather Than 100\% Tested)} \; \\$

Parameter	Symbol	Min	Тур	Max	Unit
Input Capacitance	C <sub>in</sub>	_	3	5	pF
Input/Output Capacitance	C <sub>I/O</sub>		6	8	pF

MOTOROLA FAST SRAM MCM69T618

$$<sup>\</sup>label{eq:VIL} \begin{split} ^* V_{IL} \ge & -1.5 \text{ V for } t \le t_{KHKH}/2.\\ ^{**} V_{IH} \le & V_{CC} + 1.0 \text{ V for } t \le t_{KHKH}/2. \end{split}$$

<sup>1.</sup> Device in deselected mode as defined by the Truth Table.

#### **AC OPERATING CONDITIONS AND CHARACTERISTICS**

 $(V_{CC} = 3.3 \text{ V} + 10\%, -5\%, T_{J} = 20 \text{ to } 110^{\circ}\text{C}, \text{ Unless Otherwise Noted})$ 

Input Timing Measurement Reference Level 1.5 V	Output Timing Reference Level 1.5 V
Input Pulse Levels 0 to 3.0 V	Output Load See Figure 1 Unless Otherwise Noted
Input Rise/Fall Time	

#### READ/WRITE CYCLE TIMING (See Notes 1, 2, and 3)

		МСМ69	T618–5		
Parameter	Symbol	Min	Max	Unit	Notes
Cycle Time	<sup>t</sup> KHKH	10	_	ns	
Clock High Pulse Width	<sup>t</sup> KHKL	3.5	_	ns	
Clock Low Pulse Width	<sup>t</sup> KLKH	3.5	_	ns	
Clock High to Match Valid	<sup>t</sup> KHMV	_	5	ns	
Clock Access Time	<sup>t</sup> KHQV	_	5	ns	4
Output Enable to Output Valid	<sup>t</sup> GLQV	_	5	ns	4
Match Output Enable to Match Valid	<sup>t</sup> MGLMV	_	5	ns	4
Clock High to Output Active	<sup>t</sup> KHQX1	0	_	ns	4, 5
Clock High to Output Change	<sup>t</sup> KHQX2	1.5	_	ns	4
Clock High to Match Output Change	<sup>t</sup> KHMX	1.5	_	ns	
Output Enable to Output Active	<sup>t</sup> GLQX	0	_	ns	4, 5
Match Output Enable to Match Active	<sup>t</sup> MGLMX	0	_	ns	4, 5
Output Disable to Q High–Z	<sup>t</sup> GHQZ	_	5	ns	5, 6
Match Output Disable to Match High–Z	<sup>t</sup> MGHMZ	_	5	ns	5
Clock High to Q High-Z	<sup>t</sup> KHQZ	1.5	5	ns	5, 6
Setup Times:  Address Data In Write Enable	tavkh tdvkh twvkh tevkh	2.5	_	ns	
Hold Times:  Address Data In Write Enable	<sup>†</sup> KHAX <sup>†</sup> KHDX <sup>†</sup> KHWX <sup>†</sup> KHEX	0.5	_	ns	

#### NOTES:

- 1. "Write" applies to the SW signal. "Enable" applies to SE0, SE1, and DE signals.
- 2. <u>All</u> read and write cycle timings are referenced from K or G.
- 3. G is a don't care after write cycle begins. To prevent bus contention, G should be negated prior to start of write cycle.
- 4. Tested per AC Test Load (See Figure 1).
- 5. This parameter is sampled and not 100% tested.
- 6. Measured at  $\pm$  200 mV from steady state.

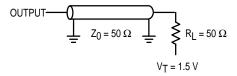
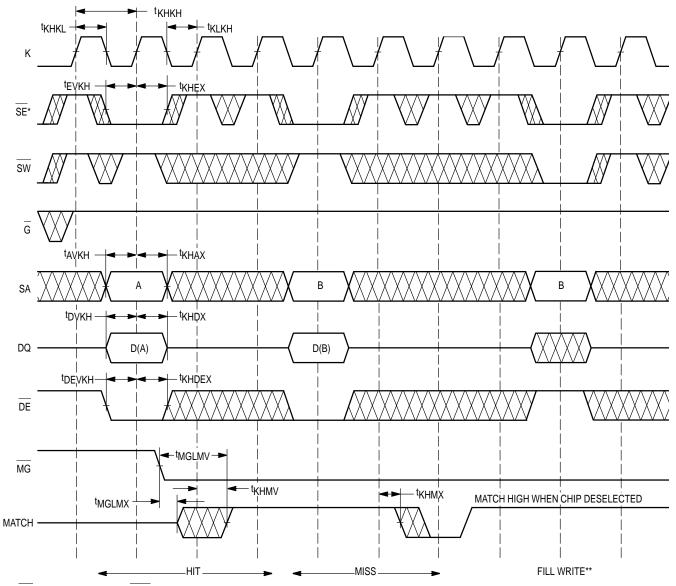


Figure 1. AC Test Loads

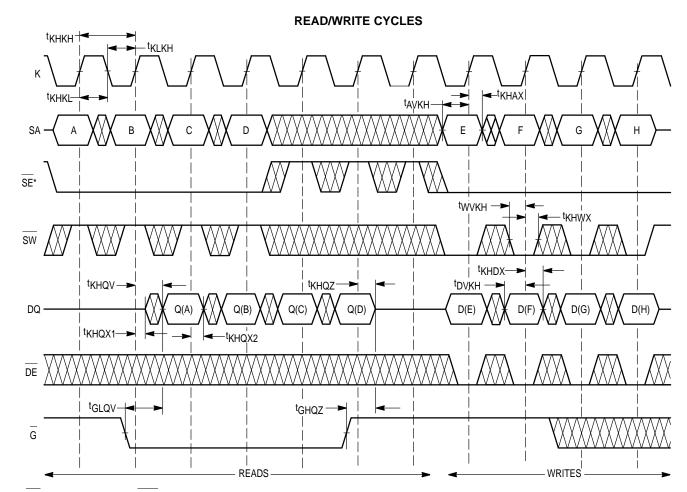
MOTOROLA FAST SRAM MCM69T618

#### **COMPARE/FILL WRITE CYCLES**



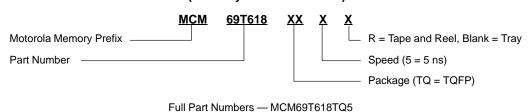
<sup>\*</sup>  $\overline{\text{SE}}$  low = SE0 high and  $\overline{\text{SE1}}$  low.

<sup>\*\*</sup> During fill write sequence, tag entry is written with tag value retained in the data input register from the previous compare cycle.



\* SE low = SE0 high and SE1 low.

## ORDERING INFORMATION (Order by Full Part Number)



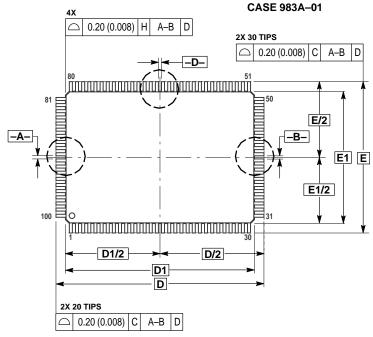
MCM69T618TQ5R

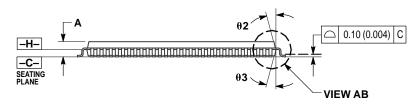
Motorola reserves the right to make changes without further notice to any products herein. Motorola makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Motorola assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters which may be provided in Motorola data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Motorola does not convey any license under its patent rights nor the rights of others. Motorola products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Motorola product could create a situation where personal injury or death may occur. Should Buyer purchase or use Motorola products for any such unintended or unauthorized application, Buyer shall indemnify and hold Motorola and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Motorola was negligent regarding the design or manufacture of the part. Motorola and manufacture of the part. Motor

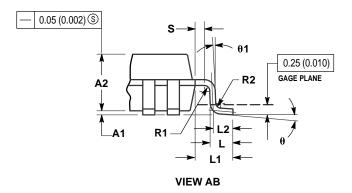
MOTOROLA FAST SRAM MCM69T618

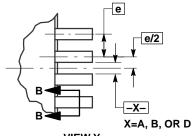
#### PACKAGE DIMENSIONS

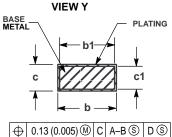
#### **TQ PACKAGE TQFP**











#### SECTION B-B

#### NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER.
   DATUM PLANE -H- IS LOCATED AT BOTTOM OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT
- THE BOTTOM OF THE PARTING LINE.

  4. DATUMS -A-, -B- AND -D- TO BE DETERMINED AT DATUM PLANE -H-.
- DIMENSIONS D AND E TO BE DETERMINED AT SEATING PLANE -C-.
- DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.25 (0.010) PER SIDE. DIMENSIONS D1 AND B1 DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE -H-.

  7. DIMENSION 6 DOES NOT INCLUDE DAMBAR
- PROTRUSION. DAMBAR PROTRUSION SHALL NOT CAUSE THE b DIMENSION TO EXCEED 0.45

	MILLIN	IETERS	INC	HES		
DIM	MIN	MAX	MIN	MAX		
Α		1.60	_	0.063		
A1	0.05	0.15	0.002	0.006		
A2	1.35	1.45	0.053	0.057		
b	0.22	0.38	0.009	0.015		
b1	0.22	0.33	0.009	0.013		
С	0.09	0.20	0.004	0.008		
c1	0.09	0.16	0.004	0.006		
D	22.00	BSC	0.866	BSC		
D1	20.00	BSC	0.787 BSC			
Е	16.00	BSC	0.630 BSC			
E1	14.00	BSC	0.551	.551 BSC		
е	0.65	BSC	0.026	BSC		
L	0.45	0.75	0.018	0.030		
L1	1.00	REF	0.039	REF		
L2	0.50	REF	0.020	REF		
S	0.20	-	0.008			
R1	0.08		0.003			
R2	0.08	0.20	0.003	0.008		
θ	0°	7°	0°	7°		
θ1	0 °		0 °			
θ2	11 °	13°	11 °	13°		
θ3	11 °	13°	11 °	13°		

Mfax is a trademark of Motorola. Inc.

USA/EUROPE/Locations Not Listed: Motorola Literature Distribution; P.O. Box 5405, Denver, Colorado, 80217. 1-303-675-2140 or 1-800-441-2447

Mfax™: RMFAX0@email.sps.mot.com - TOUCHTONE 1-602-244-6609 Motorola Fax Back System

 $\Diamond$ 

– http://sps.motorola.com/mfax/

HOME PAGE: http://motorola.com/sps/

JAPAN: Nippon Motorola Ltd.: SPD, Strategic Planning Office, 141, 4-32-1 Nishi-Gotanda, Shagawa-ku, Tokyo, Japan. 03-5487-8488

ASIA/PACIFIC: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park, - US & Canada ONLY 1-800-774-1848 51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852-26629298

**CUSTOMER FOCUS CENTER: 1-800-521-6274** 



MCM69T618/D